

In the Claims:

Please cancel claims 1-3 without prejudice or disclaimer of the subject matter contained therein.

Please add claims 6-10 as follows:

add a2

--6. A semiconductor device comprising:
a gate formed on an active region of a substrate;
a field oxide formed on the substrate adjacent the active region;
a protective layer formed on a said field oxide, said protective layer being a material different than said field oxide;
an insulating layer formed on the substrate including said gate, said field oxide and said protective layer;
a contact hole formed through said insulating layer; and
a connecting wire coupled to said gate through said contact hole.

7. The semiconductor device of claim 6, wherein said protective layer is a polysilicon layer.

8. The semiconductor device of claim 6, wherein said protective layer is formed on said field oxide only.

9. The semiconductor device of claim 6, wherein said gate is a MOSFET gate.